

PTO 1449 (modified)

ATTY DOCKET NO.
03500.010530.5

APPLICATION NO.

10/085,046

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

APPLICANT

KIYOFUMI SAKAGUCHI, ET AL.

FILING DATE

March 1, 2002

GROUP

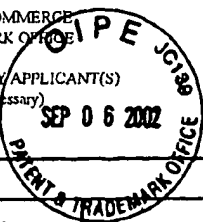
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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G	4,116,751	09/26/78	Zaromb	156	600	
	4,727,047	02/23/88	Bozler, et al.	437	89	
	5,248,621	09/28/93	Sano	437	3	
	5,250,460	10/05/93	Yamagata, et al.	437	62	
	5,277,748	01/11/94	Sakaguchi, et al.	156	630	
	5,278,092	01/11/94	Sato	437	90	
	5,278,093	01/11/94	Yonehara	437	109	
	5,285,078	02/08/94	Mimura, et al.	257	3	
	5,290,712	03/01/94	Sato, et al.	437	24	
	5,320,907	06/14/94	Sato	428	446	
	5,331,180	07/19/94	Yamada, et al.	257	3	
	5,362,683	11/08/94	Takenaka et al.	437	226	
	5,363,793	11/15/94	Sato	117	2	
	5,371,037	12/06/94	Yonehara	437	86	
	5,374,564	12/20/94	Bruehl	437	24	
	5,403,771	04/04/95	Nishida, et al.	437	89	
	5,433,168	07/18/95	Yonehara	117	90	
	5,453,394	09/26/95	Yonehara, et al.	437	62	
	5,457,058	10/10/95	Yonehara	437	24	
	5,459,081	10/17/95	Kajita	437	3	
F	5,466,631	11/14/95	Ichikawa, et al.	437	62	
EXAMINER FOURSON			DATE CONSIDERED 5/29/04			

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G	5,536,361	07/16/96	Kondo et al.	156	630.1	
	5,644,156	07/01/97	Suzuki, et al.	257	485	
	5,670,411	09/23/97	Yonchara, et al.	437	62	
	5,811,348	09/22/98	Matsushita, et al.	438	455	
	5,854,123	12/29/98	Sato, et al.	438	507	
	5,856,229	01/05/99	Sakaguchi, et al.	438	406	
	5,863,830	01/26/99	Bruel, et al.	438	478	
	5,869,387	02/09/99	Sato, et al.	438	459	
	5,970,361	10/19/99	Kumomi, et al.	438	409	
	5,980,633	11/09/99	Yamagata, et al.	117	94	
	6,103,598	08/15/00	Yamagata, et al.	438	459	
	6,107,213	08/22/00	Tayanaka	438	762	
	6,121,117	09/19/00	Sato, et al.	438	459	

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EP	0417838 A1 ✓	09/06/90	EPO			
EP	0469630 A2 ✓	02/05/92	EPO			
EP	0499488A2 ✓	02/14/92	EPO			
EP	0536790 A2 ✓	04/14/93	EP			
EP	0553852 A2 ✓	08/04/93	EPO			
EP	0553859 A3 ✓	08/04/93	EPO			

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5/29/04

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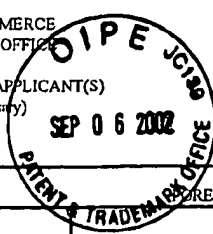
March 1, 2002


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G	EP	0553860 A2 ✓	08/04/93	EPO			
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	EP	0793263 A2 ✓	09/97	EPO			
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	JP	62-108539 ✓	05/19/87	Japan			Abstract
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	JP	03-70156 ✓	03/26/91	Japan			Abstract
	JP	05-211128 ✓	08/20/93	Japan			Abstract
	JP	05-283722 ✓	10/29/93	Japan			Translation
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	JP	07-79016 ✓	03/20/95	Japan			Abstract
	JP	07-211602 ✓	08/11/95	Japan			Abstract
	JP	07-302889 ✓	11/14/95	Japan			Abstract
G	JP	07-326719 ✓	12/12/95	Japan			Abstract
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G	JP	9-162090	06/20/97	Japan		Abstract	
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G	✓ T. Ahe et al. "Silicon Kesshou to Doping (Silicon Crystal and Doping)", Maruzen Co., Ltd., 1986 (with partial translation)						
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	✓ G.W. Cullen, ed., Journal of Crystal Growth, vol. 63, no. 3, pp. 429-590, Oct. 1993 (see p. 547.)						
	✓ Extended Abstracts (the 57 th Autumn Meeting, 1996); The Japan Society of Applied Physics (Abstr. 8a-V-8) (with translation)						
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	✓ Y. Hashimoto, "Shin-Kagaku Yougo Jiten" (new chemical term dictionary), Sankyo Shuppan Co., Ltd., 6 th Edn (1973) (definition of anodic oxidation) (with translation)						
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G	✓ K. Imai et al., "Crystalline Quality of Silicon Layer Formed by FIPOS Technology," J. of Crystal Growth 63, 547-553 (1983)						
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G	✓	T. Ito et al. "Porous Silicon Crystal Prepared by Anodization", <u>Applied Physics</u> (Japanese) vol. 57 no. 11 (1988) (no translation)	
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	✓	W.P. Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review", J. Electrochem. Soc., vol. 138, No. 1, pp. 340-47 (1991)	
	✓	Kazutoshi Nagano, et al., "Oxidized Porous Silicon and It's Application", Semiconductor Research Lab Matsushita Electric Industrial Co., Ltd. (no translation)	
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	✓	K. Ogasawara, et al., "Enhancement of Electroluminescence from n-Type Porous Silicon and Its Photoelectrochemical Behavior", J. Electrochem. Soc., vol. 142, no. 6, pp.1874-79 (1995)	
	✓	M. Ohnishi, et al., "New Type Structures Of A-Si Solar Cell Submodules Fabricated By Microscopic Hole Spacing Technique", Record of the Photovoltaic Specialist Conference, Kissimimee, May 21-25, 1990, vol. 2, No. Conf. 21, pp. 1394-1399, May 21, 1990.	
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G	✓	T. Yonehara et al., "Epitaxial layer transfer by bond and etch back of porous Si", <u>Appl. Phys. Lett.</u> 64(16), 2108-2110 (1994)	
EXAMINER FOURSON		DATE CONSIDERED 5/29/04	

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Sheet 5 of 5

FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary) Submitted: October 21, 2003		ATTY DOCKET NO. 03500.0105305		APPLICATION NO. 10/085,046	
		APPLICANT KIYOFUMI SAKAGUCHI, ET AL.			
		FILING DATE March 1, 2002		GROUP 2823	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	

FOREIGN PATENT DOCUMENTS							
DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT		
<i>G</i> 5-217981	8/27/93	Japan			Abstract		
<i>G</i> 5-217827	8/27/93	Japan			Abstract		
<i>G</i> 0 553 861 A1	8/04/93	Europe					

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)		

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